Enhanced Figure of Merit in Molecular Junctions

BAADJI Nadjib

LPMA, Physics department university of Mohamed Boudiaf- M'Sila, M'sila, Algeria

ABSTRACT

In order to convert the wasted heat into useful energy, thermoelectric devices are designed to maximize the figure of merit ZT defined as the ratio of the electric and thermal conductivity times the Seebeck coefficient. However, most of devices suffer from the small value ofZT (ZT < 1) and use mostly doped semiconductors. Here, we show that molecular junctions can have higher value of ZT, paving the way for efficient thermoelectric devices. Using the density functionaltheory combined with non-equilibrium Green's function, we calculate, in linear response regime andLandauer-Buttiker approach, the figure of merit for different types of junctions. The molecular junctions have values of ZT > 3 and can be increased by an order of magnitude by different physicaland chemical means.

References

P10

- [1] P. Gehring *et al.* "Complete mapping of the thermoelectric properties of a single molecule" Nature Nanotechnology, **16**, 426 (2021).
- [2] P. Gehring, J. M. Thijssen, & H. S. van der Zant, "Single-molecule quantum-transport phenomena inbreak junctions". Nat. Rev. Phys. **1**, 381–396 (2019).
- [3] B. K. Agarwalla, J.-H. Jiang & D. Segal, "Thermoelectricity in molecular junctions with harmonic and anharmonic modes". Beilstein J. Nanotechnol. **6**, 2129 (2015).
- [4] M. Di Ventra, "Electrical Transport in Nanoscale Systems", Cambridge University Press: New York, NY,USA, (2008).
- [5] R. Berman "Thermal Conduction in Solids", Clarendon Press, Oxford, UK, 1976
- [6] G. Cuniberti, G. Fagas, K. Richter, K. (Eds.) "Introducing Molecular Electronics", Springer: New York, NY, USA, (2005).

